



SNS COLLEGE OF ENGINEERING



DEPARTMENT OF ELECTRONICS & COMMUNICATION ENGINEERING

19EC505-VLSI DESIGN

III YEAR/₁ V SEMESTER

UNIT 1 -MOS TRANSISTOR PRINCIPLE

CMOS INVERETER DC CHARACTERISTICS



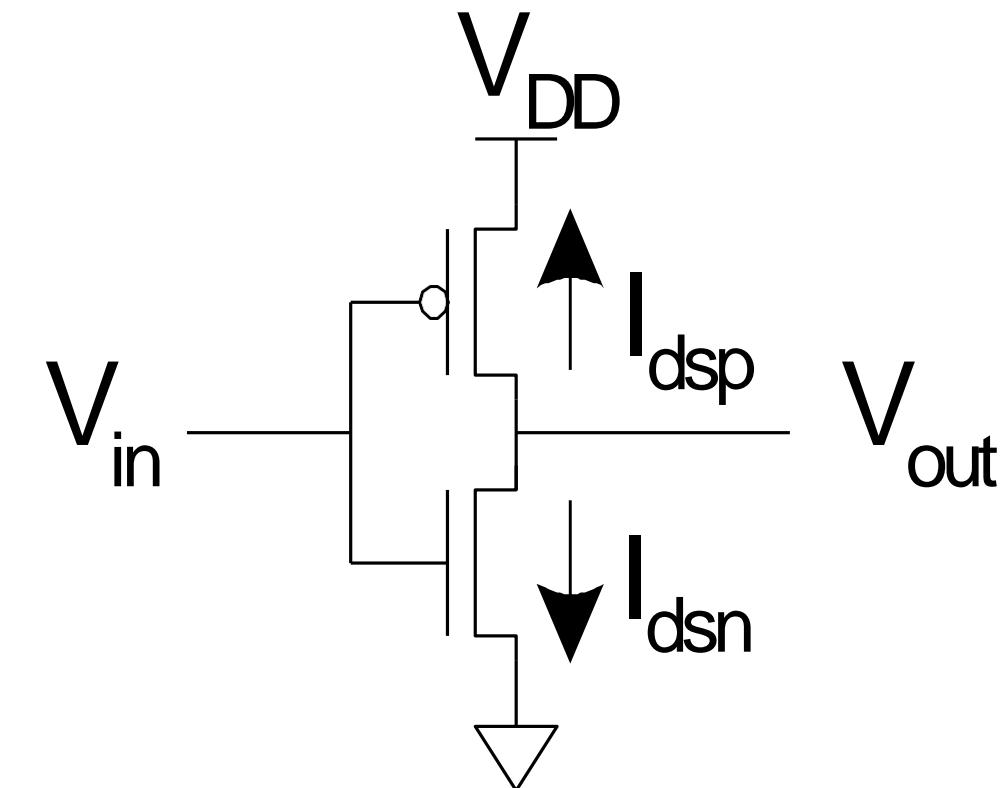
OUTLINE



- INTRODUCTION
- DC RESPONSE
- LOGIC LEVELS AND NOISE MARGINS
- ACTIVITY
- TRANSIENT RESPONSE
- ASSESSMENT
- SUMMARY

DC RESPONSE

- DC Response: V_{out} vs. V_{in} for a gate
- Ex: Inverter
 - When $V_{in} = 0 \rightarrow V_{out} = V_{DD}$
 - When $V_{in} = V_{DD} \rightarrow V_{out} = 0$
 - In between, V_{out} depends on transistor size and current
 - By KCL, must settle such that $I_{dsn} = |I_{dsp}|$
 - We could solve equations
 - But graphical solution gives more insight





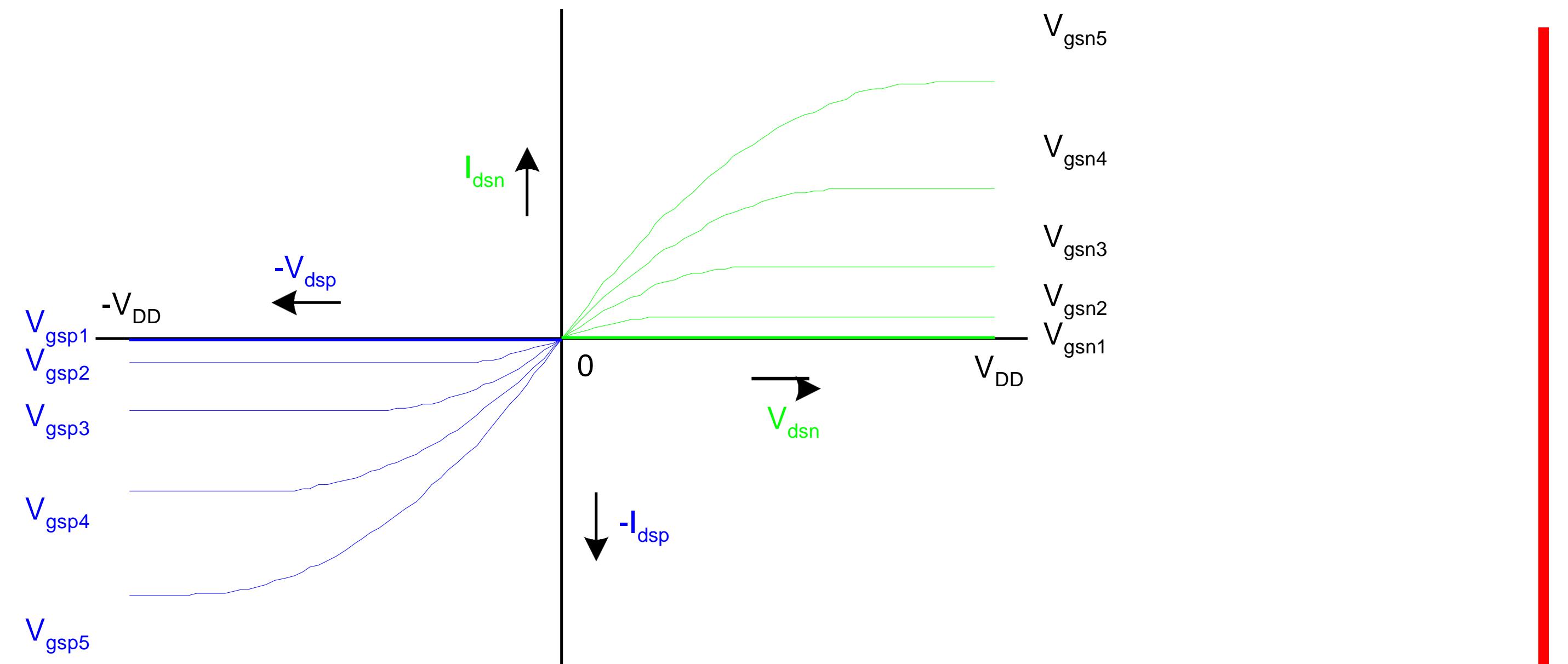
TRANSISTOR OPERATION



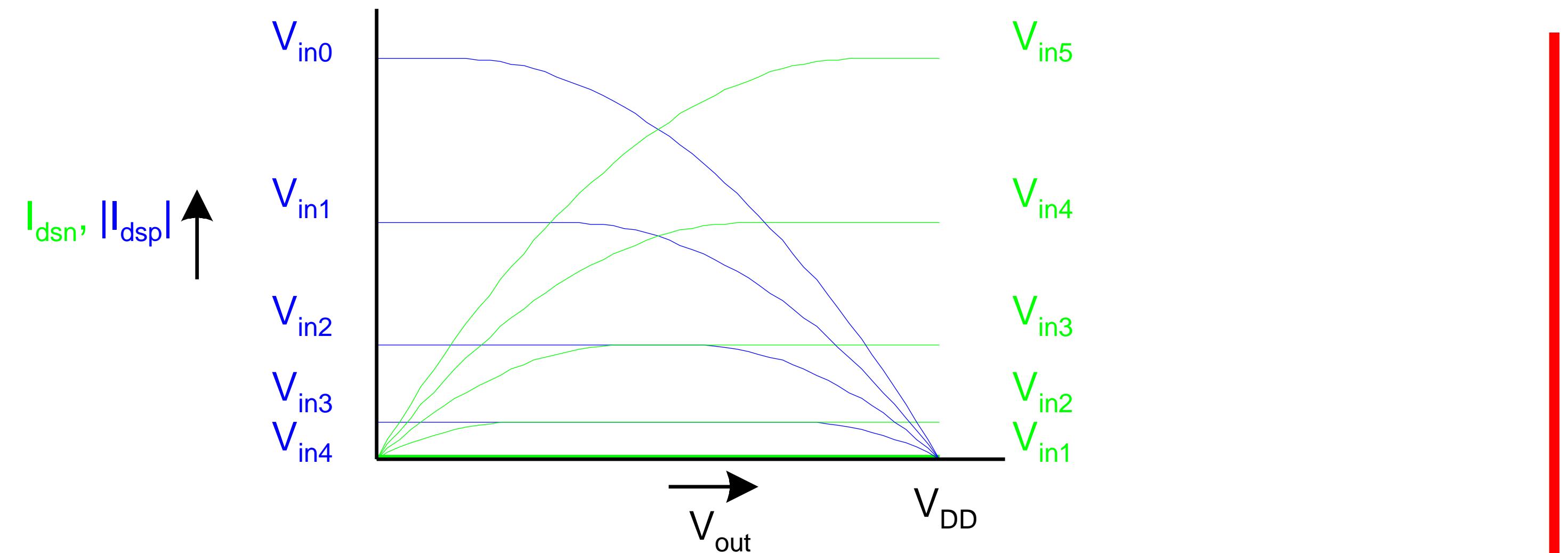
- Current depends on region of transistor behavior
- For what V_{in} and V_{out} are nMOS and pMOS in
 - Cutoff?
 - Linear?
 - Saturation?

I-V CHARACTERISTICS

Make pMOS is wider than nMOS such that $\beta_n = \beta_p$

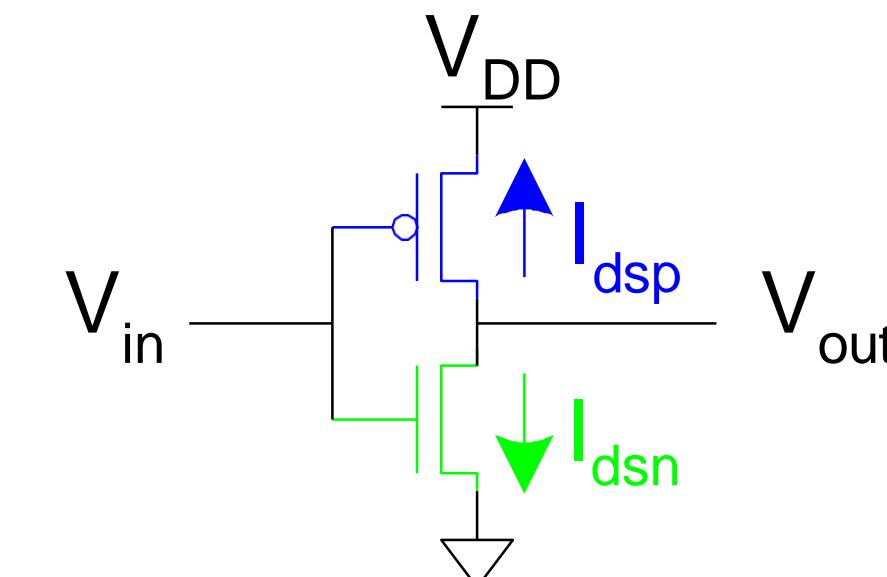
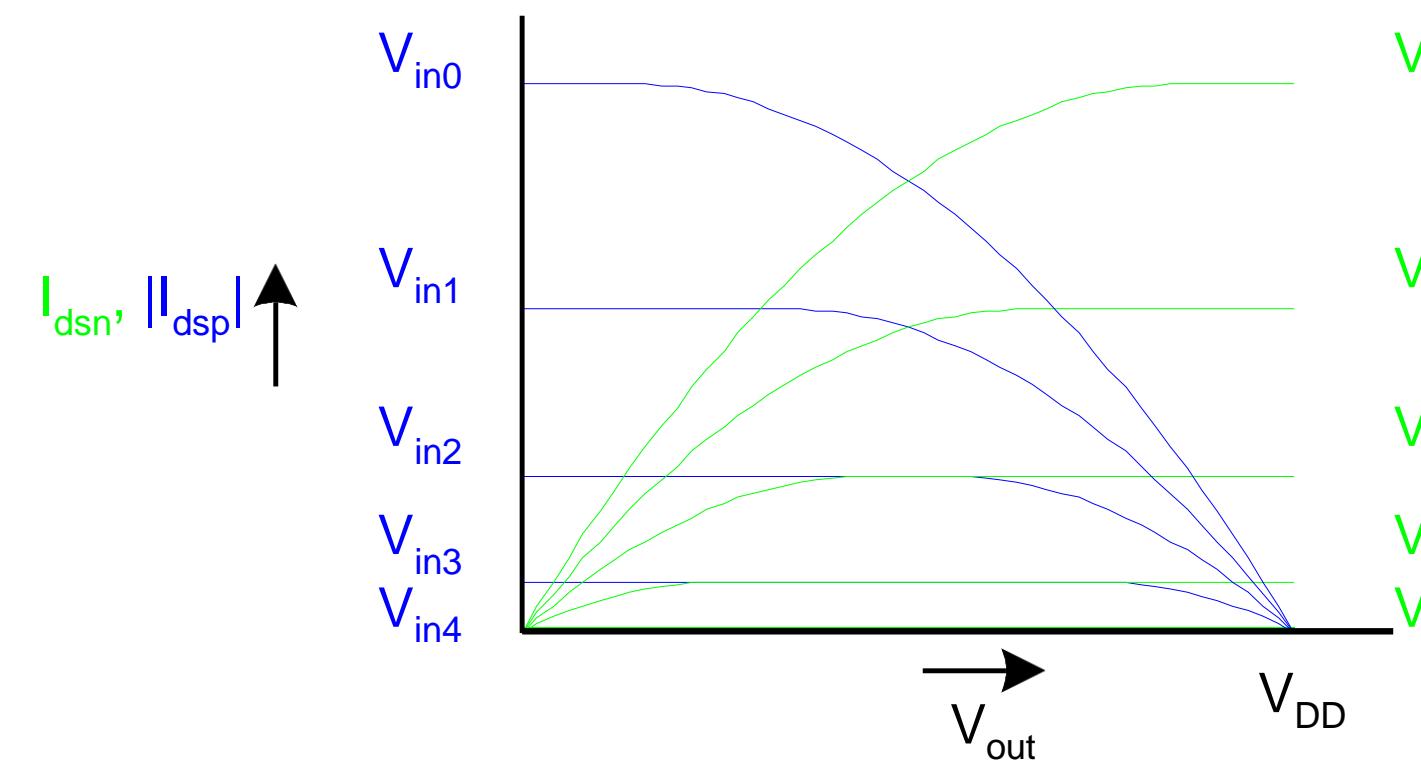


CURRENT VS V_{OUT} , V_{IN}



LOAD LINE ANALYSIS

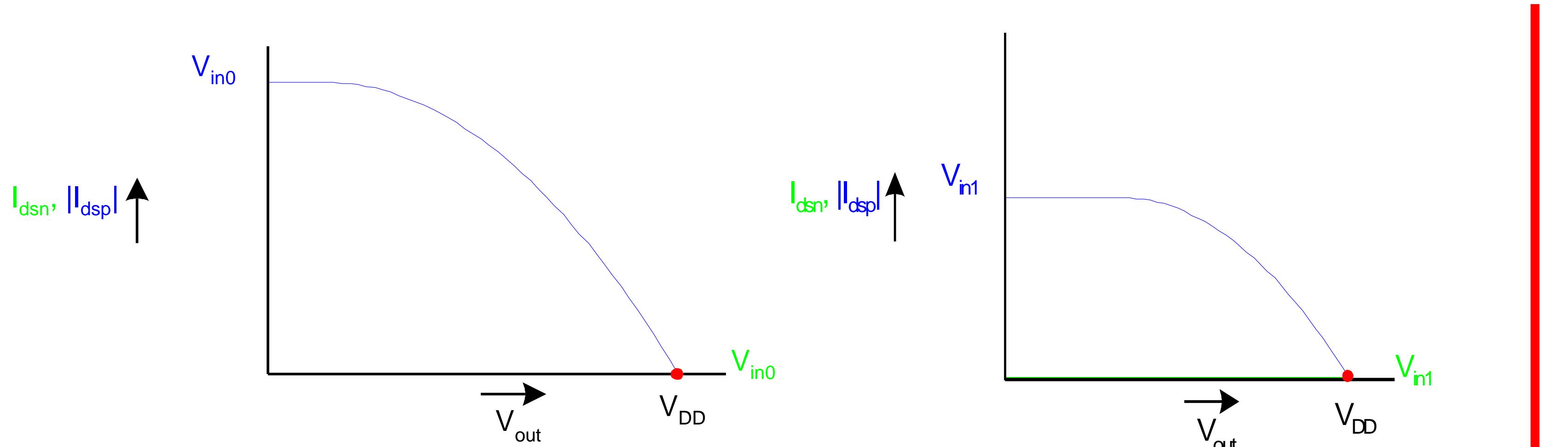
- For a given V_{in} :
 - Plot I_{dsn} , I_{dsp} vs. V_{out}
 - V_{out} must be where |currents| are equal in



LOAD LINE ANALYSIS

$$V_{in} = 0$$

$$V_{in} = 0.2V_{DD}$$



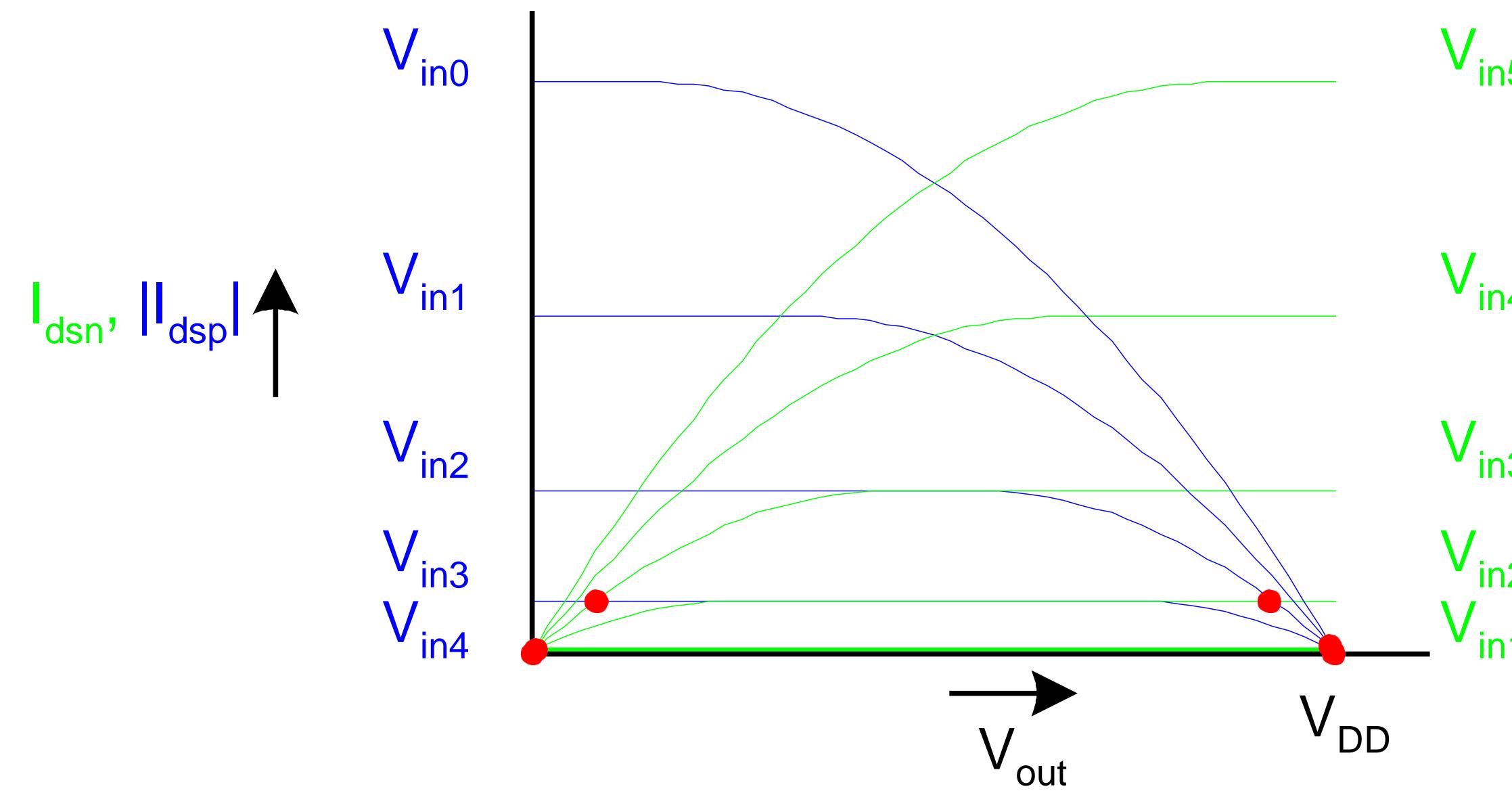


ACTIVITY-BRAIN TEASERS



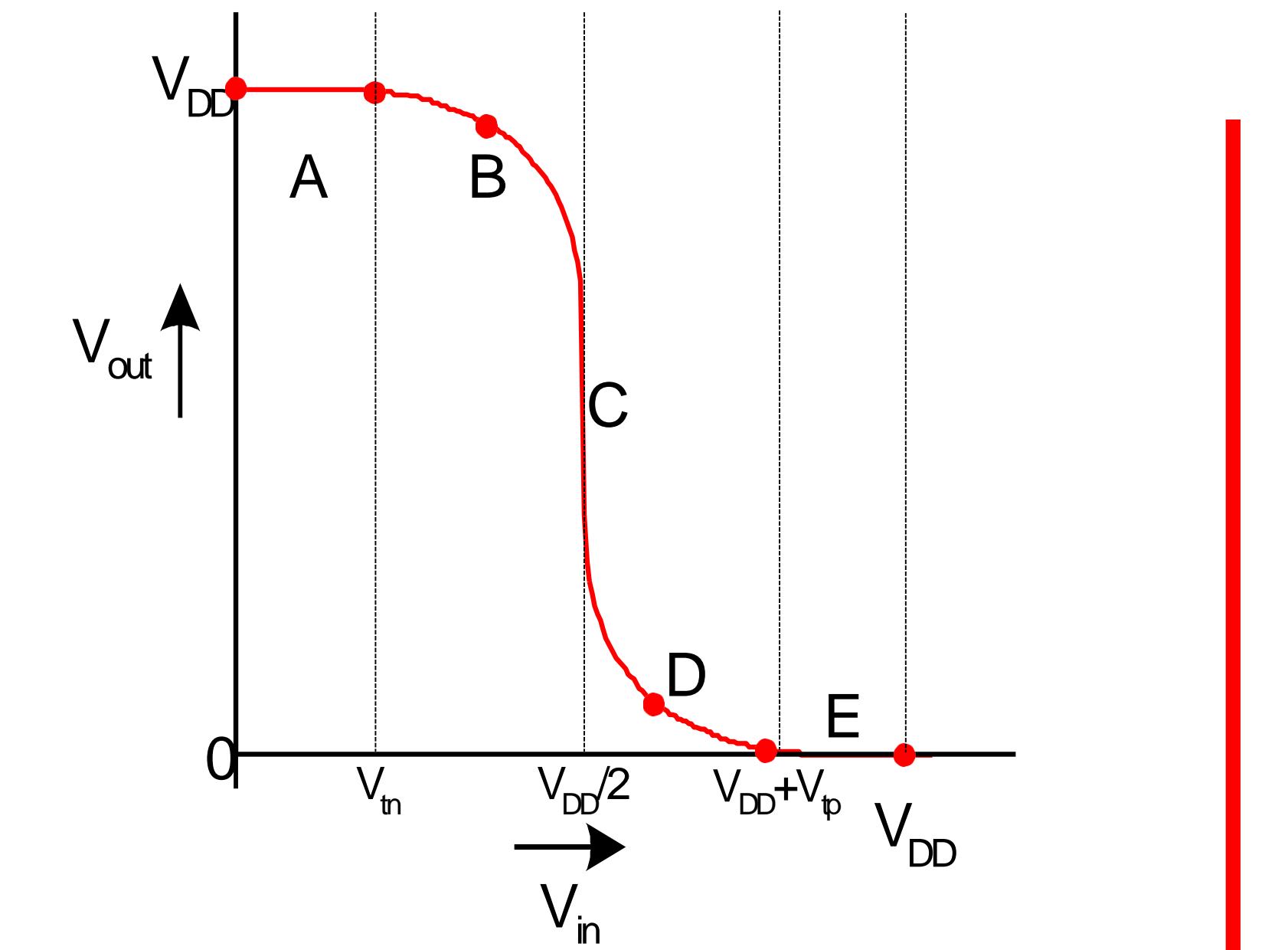
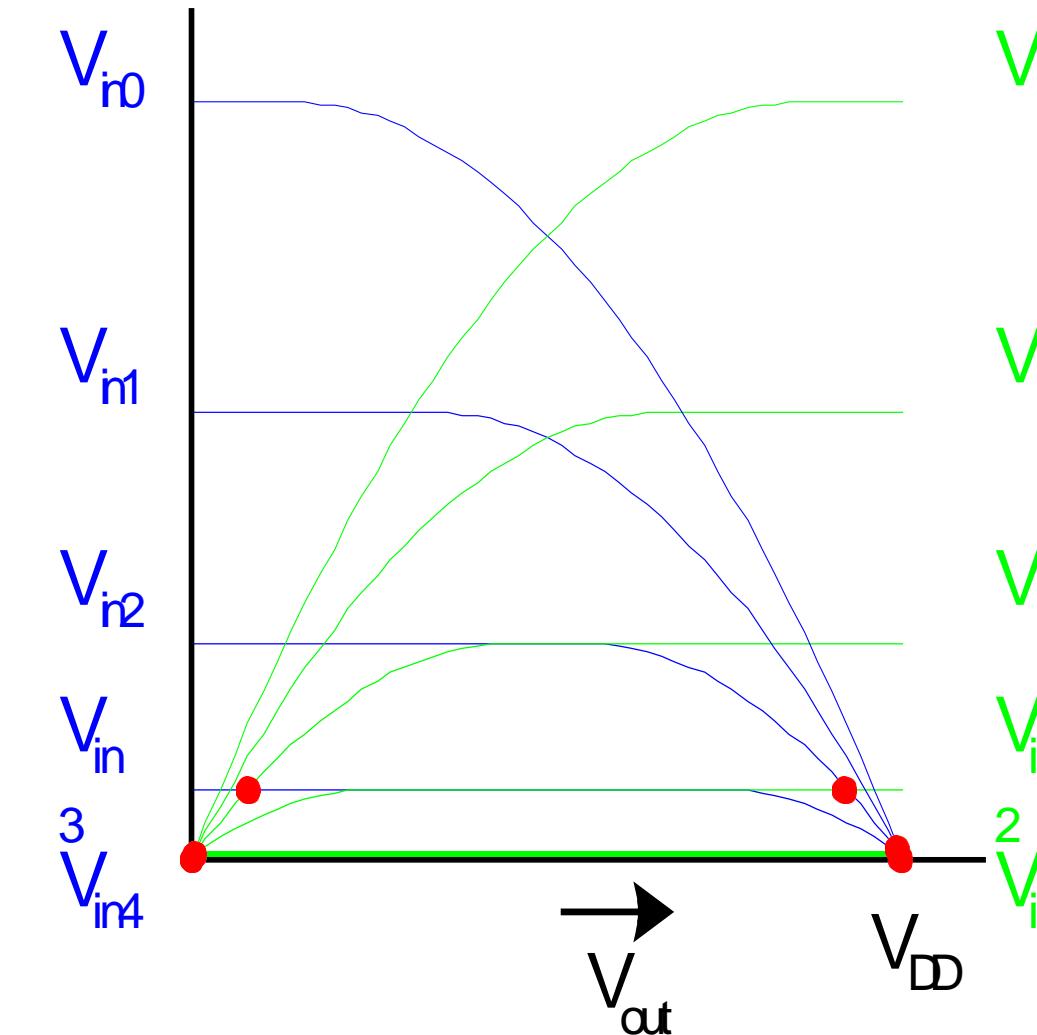
1 <i>safes o r t y</i>	2 FUSS ○	3 cake pineapple	4 — TIK ○
5 • L D	6 TILL IME	7 JOB AN	8 WORL
9 P P O D	10 INITIA _	11 FILE	12 JUS 144 TICE
13 WOHNICLEE	14 L O V	15 1 T 3 4 5 6	16 BRING BALLERINAS

LOAD LINE ANALYSIS SUMMARY



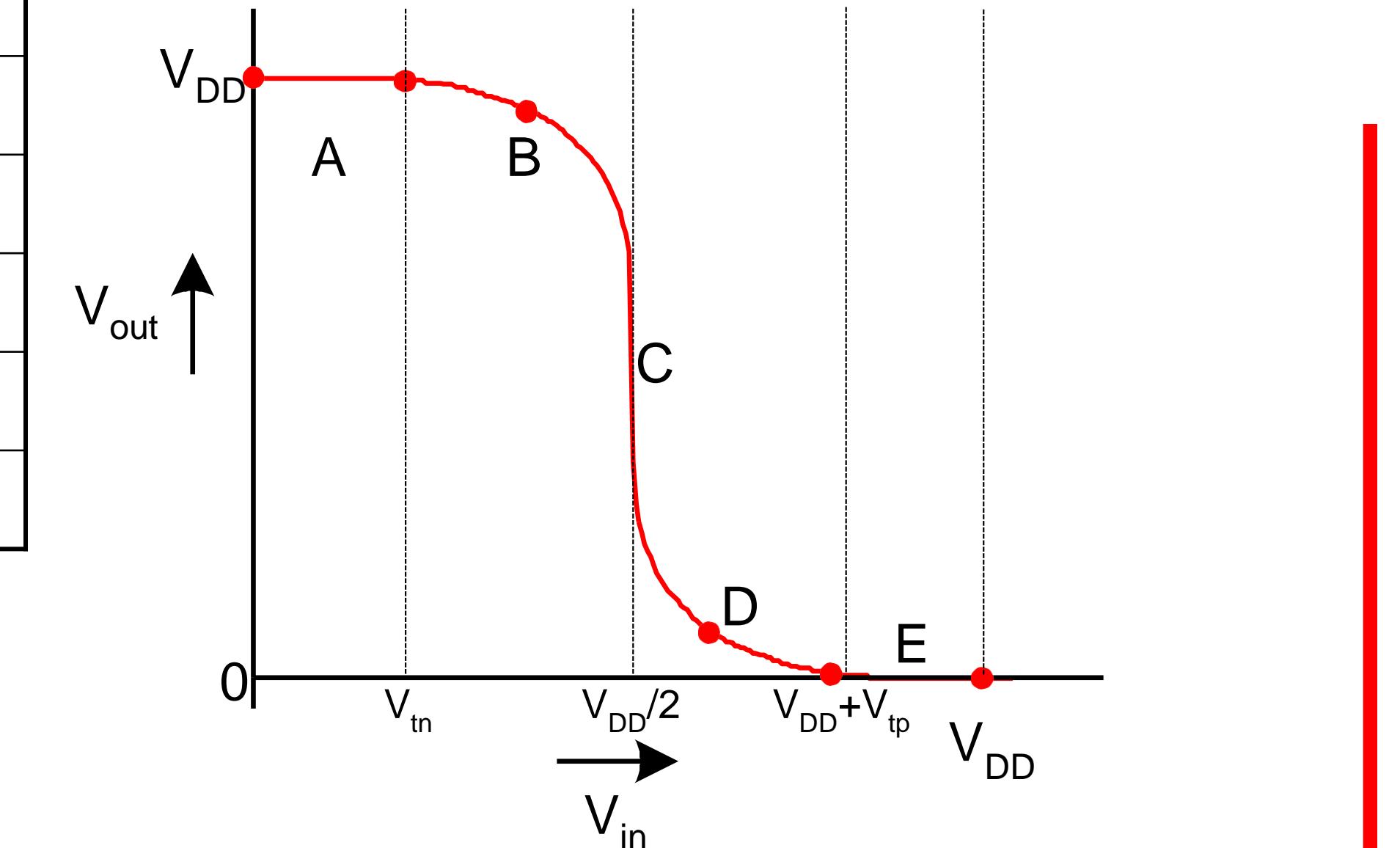
DC TRANSFER CURVE

Transcribe points onto V_{in} vs. V_{out} plot



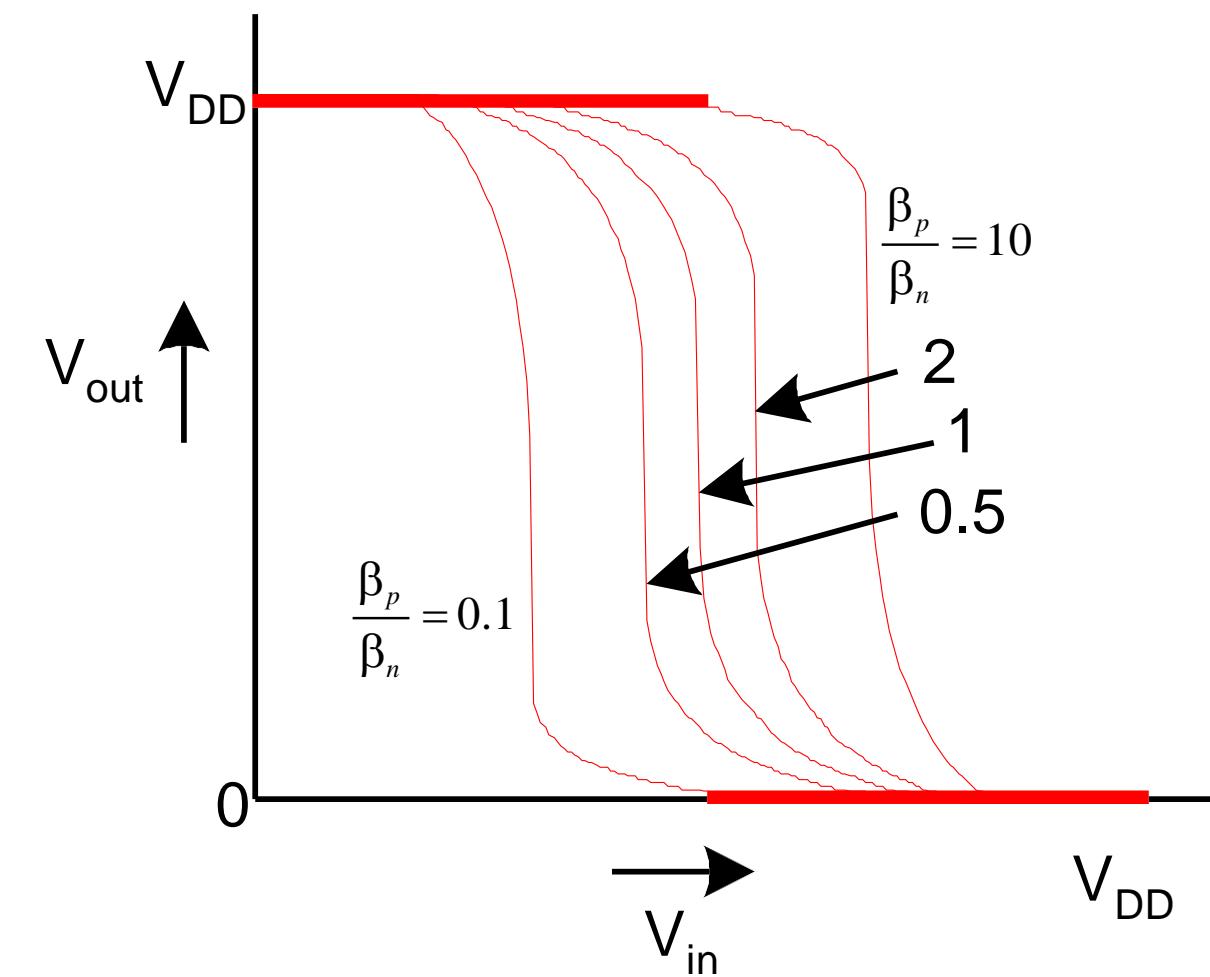
REVISIT TRANSISTOR OPERATING REGIONS

Region	nMOS	pMOS
A	Cutoff	Linear
B	Saturation	Linear
C	Saturation	Saturation
D	Linear	Saturation
E	Linear	Cutoff



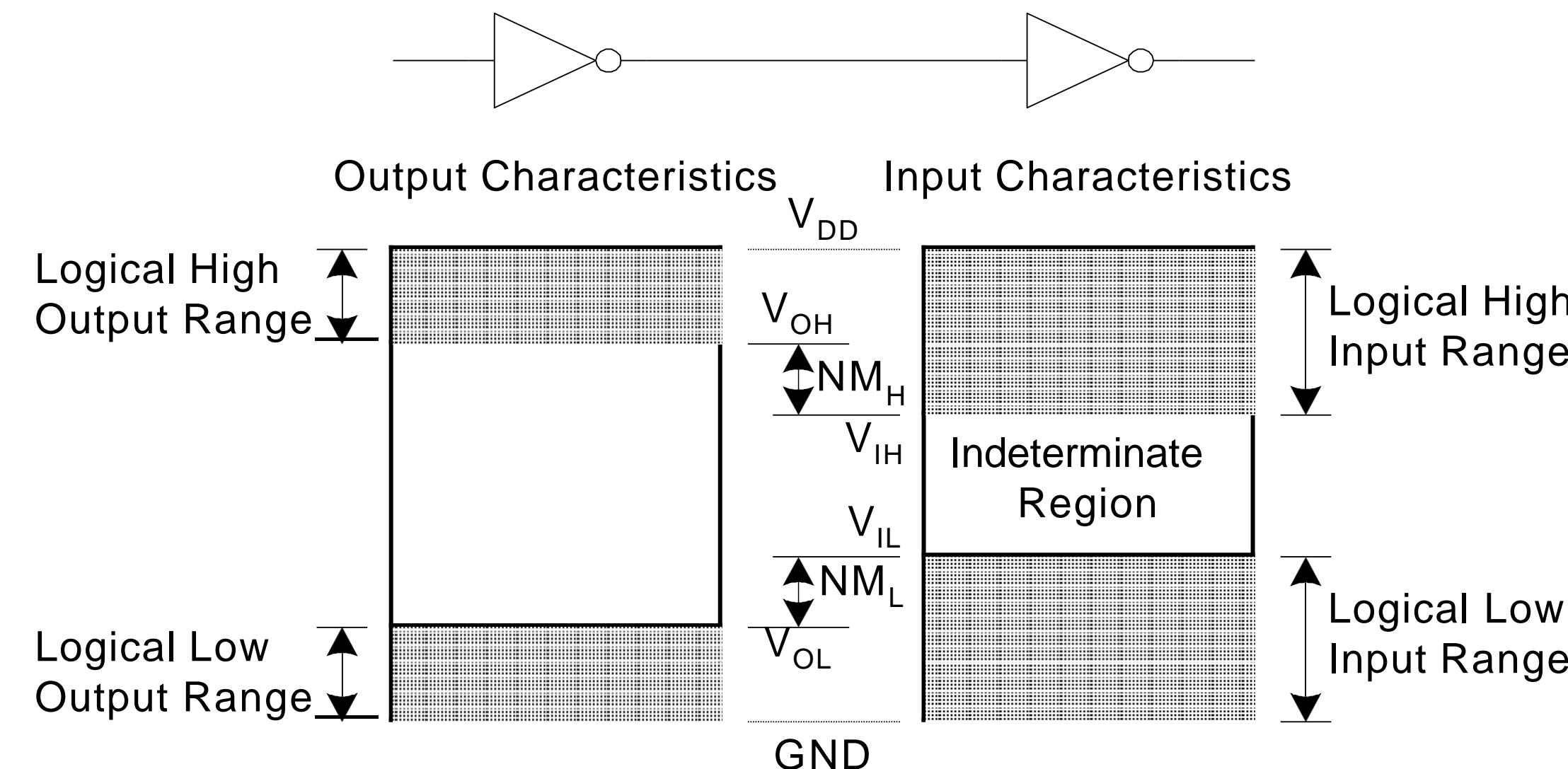
BETA RATIO

If $\beta_p / \beta_n \neq 1$, switching point will move from $V_{DD}/2$ Called skewed gate
Other gates: collapse into equivalent inverter



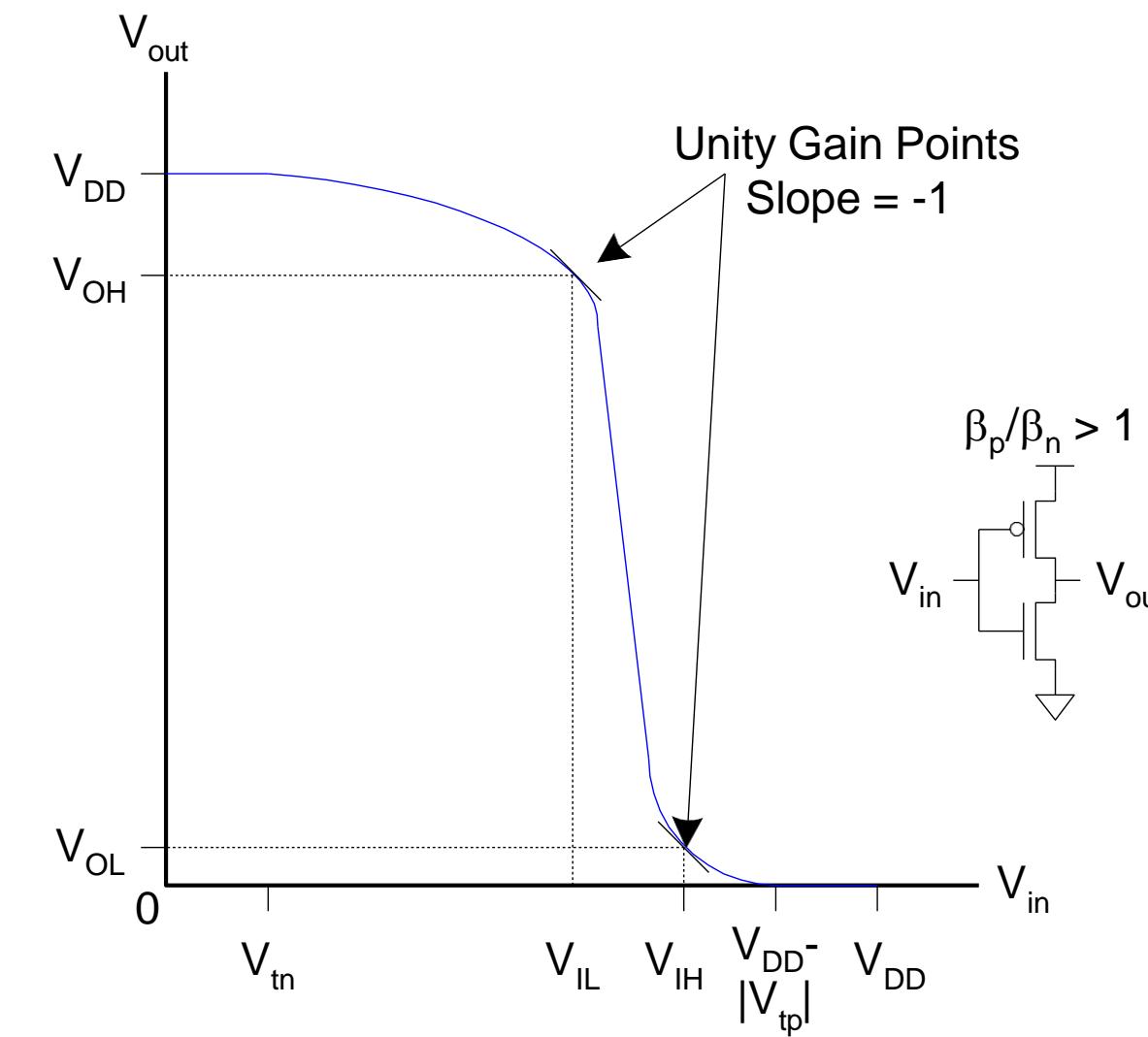
NOISE MARGINS

How much noise can a gate input see before it does not recognize the input?



LOGIC LEVELS

To maximize noise margins, select logic levels at unity gain point of DC transfer characteristic



TRANSIENT RESPONSE

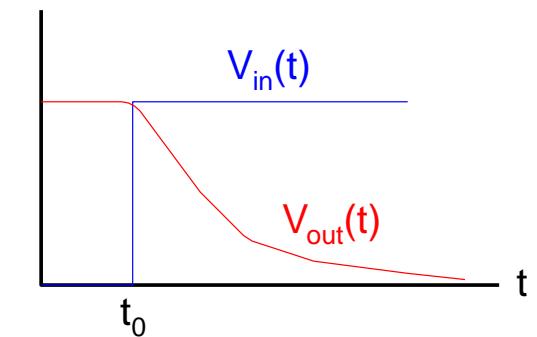
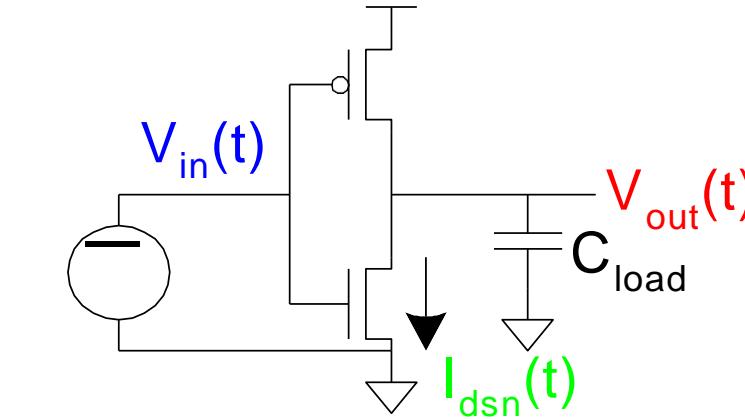
- DC analysis tells us V_{out} if V_{in} is constant
- Transient analysis tells us $V_{out}(t)$ if $V_{in}(t)$ changes
 - Requires solving differential equations
- Input is usually considered to be a step or ramp
 - From 0 to V_{DD} or vice versa

$$V_{in}(t) = u(t - t_0)V_{DD}$$

$$V_{out}(t < t_0) = V_{DD}$$

$$\frac{dV_{out}(t)}{dt} = -\frac{I_{dsn}(t)}{C_{load}}$$

$$I_{dsn}(t) = \begin{cases} 0 & t \leq t_0 \\ \frac{\beta}{2}(V_{DD} - V)^2 & V_{at} > V_{DD} - V_t \\ \beta \left(V_{DD} - V_t - \frac{V_{at}(t)}{2} \right) V_{at}(t) & V_{at} < V_{DD} - V_t \end{cases}$$





ASSESSMENT

- 1) If the width of a transistor increases, the current will
increase decrease not change
- 2) If the length of a transistor increases, the current will
increase decrease not change
- 3) If the supply voltage of a chip increases, the maximum transistor current will
increase decrease not change
- 4) If the width of a transistor increases, its gate capacitance will
increase decrease not change
- 5) If the length of a transistor increases, its gate capacitance will
increase decrease not change
- 6) If the supply voltage of a chip increases, the gate capacitance of each transistor will
increase decrease not change

ACTIVITY

- 1) If the width of a transistor increases, the current will
increase **decrease** **not change**
- 2) If the length of a transistor increases, the current will
increase **decrease** **not change**
- 3) If the supply voltage of a chip increases, the maximum transistor current will
increase **decrease** **not change**
- 4) If the width of a transistor increases, its gate capacitance will
increase **decrease** **not change**
- 5) If the length of a transistor increases, its gate capacitance will
increase **decrease** **not change**
- 6) If the supply voltage of a chip increases, the gate capacitance of each transistor will
increase **decrease** **not change**